DMA26102

Silicon PNP epitaxial planar type

For digital circuits

Features

- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Basic Part Number

Dual DRA2124E (Common emitter)

Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

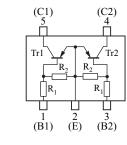
Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V _{CBO}	-50	V
Collector-emitter voltage (Base open)	V _{CEO}	-50	V
Collector current	I _C	-100	mA
Total power dissipation	P _T	300	mW
Junction temperature	Tj	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Package

Code

- Mini5-G3-B
- Pin Name
 - 1: Base (Tr1) 4: Collector (Tr2)
 - 2: Emitter (Common) 5: Collector (Tr1)
 - 3: Base (Tr2)
- Marking Symbol: F4

Internal Connection



Resistance value	R ₁	22	kΩ
	R ₂	22	kΩ

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

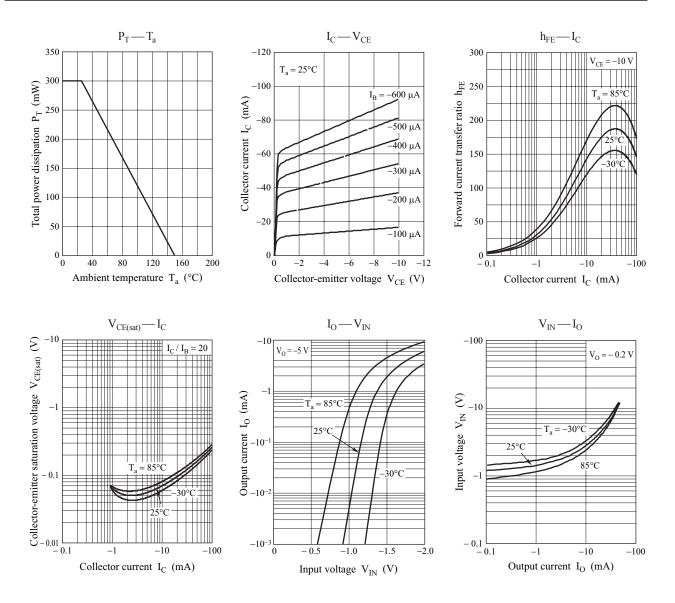
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \ \mu {\rm A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 {\rm mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{\rm CB} = -50$ V, $I_{\rm E} = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{\rm CE} = -50$ V, $I_{\rm B} = 0$			-0.5	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\rm EB} = -6$ V, $I_{\rm C} = 0$			- 0.2	mA
Forward current transfer ratio	\mathbf{h}_{FE}	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	60			
h _{FE} ratio *	h _{FE} (Small/Large)	$V_{CE} = -10 \text{ V}, I_C = -5 \text{ mA}$	0.50	0.99		
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	V _{I(on)}	$V_{CE} = -0.2 \text{ V}, I_C = -5 \text{ mA}$	-2.6			V
Input voltage (OFF)	V _{I(off)}	$V_{CE} = -5 \text{ V}, I_C = -100 \mu\text{A}$			- 0.8	V
Input resistance	R ₁		-30%	22	+30%	kΩ
Resistance ratio	R ₁ / R ₂		0.8	1.0	1.2	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Ratio between 2 elements

DMA26102

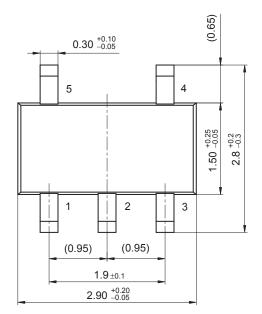
Panasonic

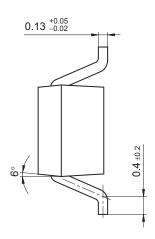


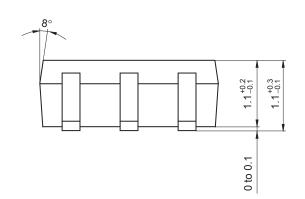
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Mini5-G3-B

Unit: mm







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